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Product data sheet

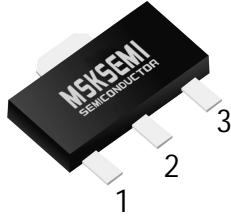
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FEATURES

- High Collector Current
- Complementary to SS8050

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-40	V
V_{CE0}	Collector-Emitter Voltage	-25	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.5	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}C/W$
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$

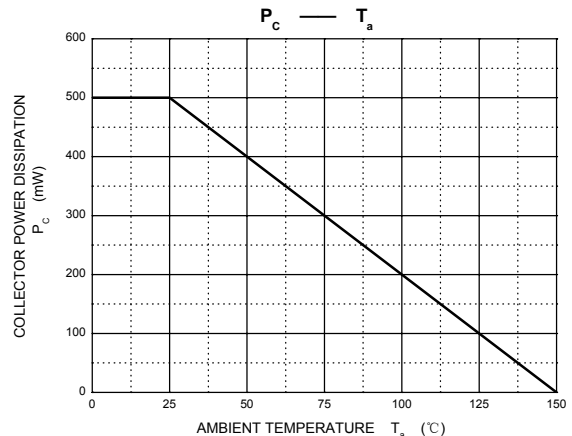
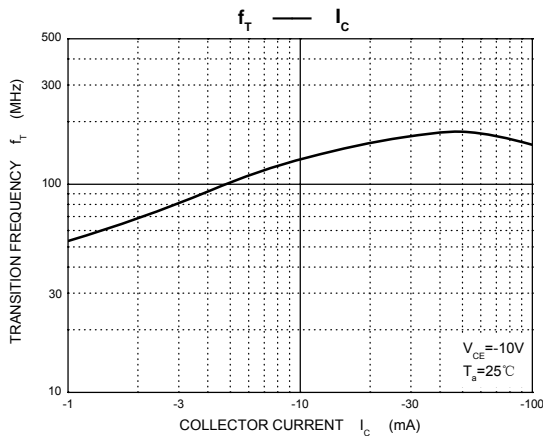
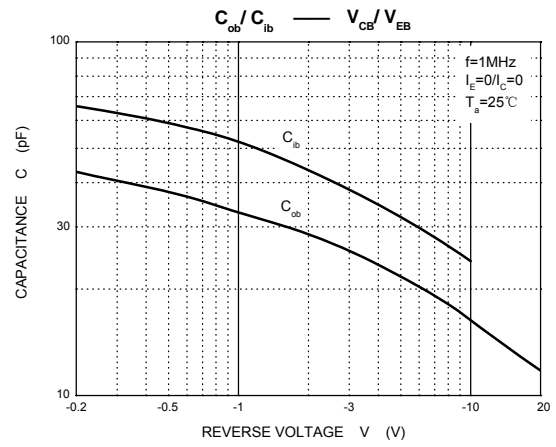
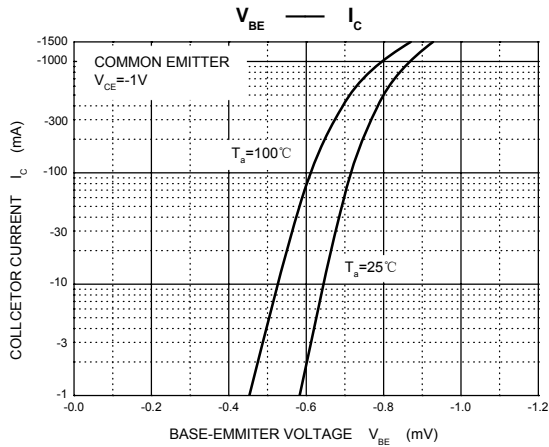
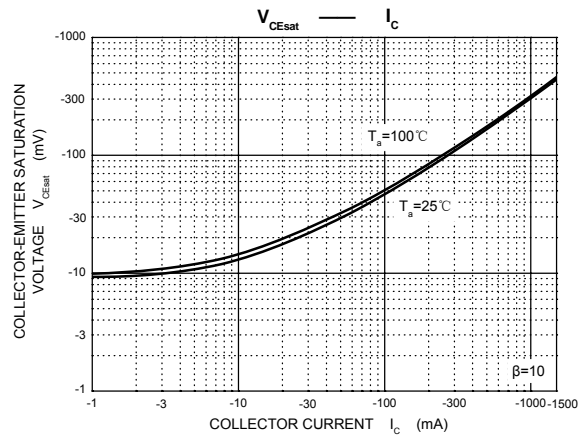
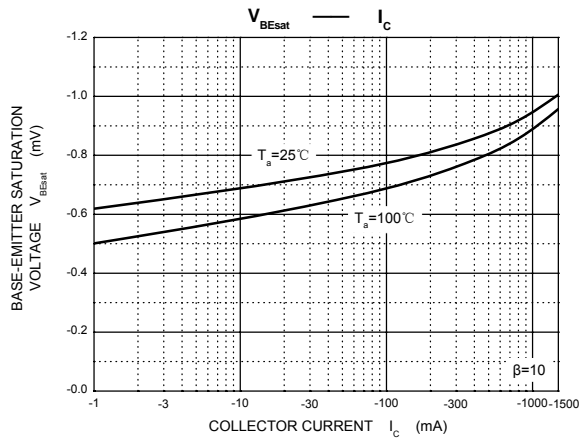
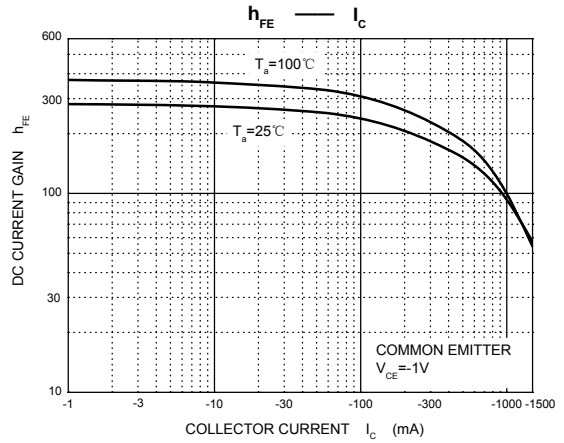
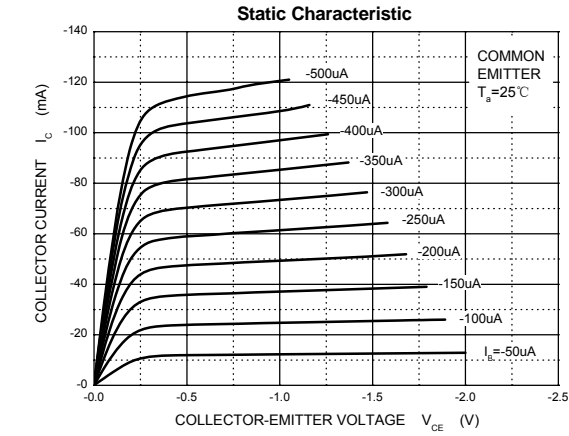
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C=-1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CB0}	$V_{CB}=-40V, I_E=0$			-100	nA
Emitter cut-off current	I_{EB0}	$V_{EB}=-5V, I_C=0$			-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	120		400	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$			-1	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA, f=30MHz$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			20	pF

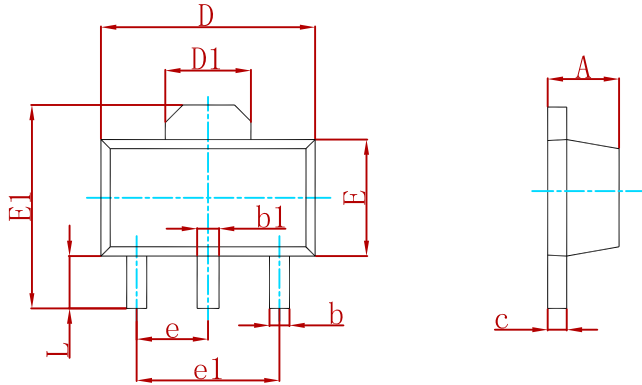
CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120 - 200	200 - 350	300 - 400

Typical Characteristics

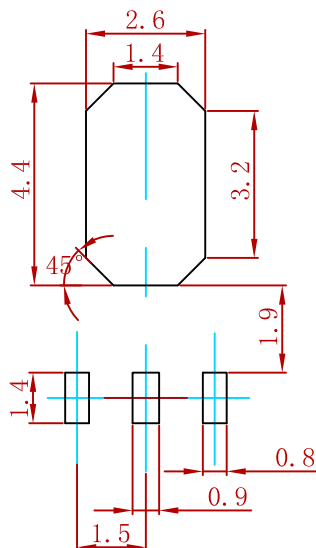


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SS8550	SOT-89	1000

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